

**Vishay Siliconix** 

# P-Channel 12 V (D-S) MOSFET

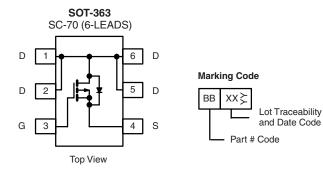
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	<b>R<sub>DS(on)</sub> (Ω)</b>	I <sub>D</sub> (A)		
- 12	0.085 at V <sub>GS</sub> = - 4.5 V	- 3.3		
	0.115 at V <sub>GS</sub> = - 2.5 V	- 2.9		
	0.160 at V <sub>GS</sub> = - 1.8 V	- 2.4		

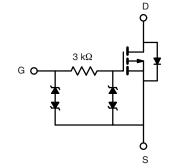
#### FEATURES

- Halogen-free According to IEC 61249-2-21
  Definition
- TrenchFET<sup>®</sup> Power MOSFET: 1.8 V Rated
- ESD Protected: 3000 V
- Thermally Enhanced SC-70 Package
- Compliant to RoHS Directive 2002/95/EC

#### **APPLICATIONS**

- Load Switching
- PA Switch
- Level Switch





Ordering Information: Si1417EDH-T1-E3 (Lead (Pb)-free) Si1417EDH-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	A = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	- 12		V
Gate-Source Voltage		V <sub>GS</sub>	± 12		
Continuous Drain Current /T 150 °C)ª	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	- 3.3	- 2.7	А
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 85 °C		- 2.4	- 1.9	
Pulsed Drain Current		I <sub>DM</sub>	- 8		A
Continuous Diode Current (Diode Conduction) <sup>a</sup>		۱ <sub>S</sub>	- 1.4	- 0.9	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	- P <sub>D</sub>	1.56	1.0	W
	T <sub>A</sub> = 85 °C		0.81	0.52	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 5 s	- R <sub>thJA</sub> R <sub>thJF</sub>	60	80		
	Steady State		100	125	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State		34	45		

Notes:

a. Surface mounted on 1" x 1" FR4 board.



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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static				•			
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$	- 0.45			V	
Gate-Body Leakage	I <sub>GSS</sub> -	$V_{DS} = 0 \text{ V}, \text{ V}_{GS} = \pm 4.5 \text{ V}$			± 1.5	μA	
		$V_{DS} = 0 V, V_{GS} = \pm 12 V$			± 10	mA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -9.6 \text{ V}, V_{GS} = 0 \text{ V}$		- 1			
		$V_{DS}$ = - 9.6 V, $V_{GS}$ = 0 V, $T_{J}$ = 85 °C			- 5	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 V$ , $V_{GS} = -4.5 V$	- 4			А	
Drain-Source On-State Resistance <sup>a</sup>		$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -3.3 \text{ A}$		0.070	0.085	Ω	
	R <sub>DS(on)</sub>	$V_{GS} = -2.5 \text{ V}, \text{ I}_{D} = -2.9 \text{ A}$		0.095	0.115		
		$V_{GS} = -1.8 \text{ V}, \text{ I}_{D} = -1.0 \text{ A}$		0.133	0.160		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 3.3 A		8		S	
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = - 1.4 A, V <sub>GS</sub> = 0 V		- 0.80	- 1.1	V	
Dynamic <sup>b</sup>							
Total Gate Charge	Qg			5.8	8	nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ = - 6 V, $V_{GS}$ = - 4.5 V, $I_{D}$ = - 3.3 A		1.3			
Gate-Drain Charge	Q <sub>gd</sub>			1.5			
Turn-On Delay Time	t <sub>d(on)</sub>			0.60	1.0		
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 6 V, $R_L$ = 6 $\Omega$		1.4	2.1	- μs	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 1 Å, $V_{GEN}$ = - 4.5 V, $R_g$ = 6 $\Omega$		4.9	7.5		
Fall Time	t <sub>f</sub>			4.9	7.5		

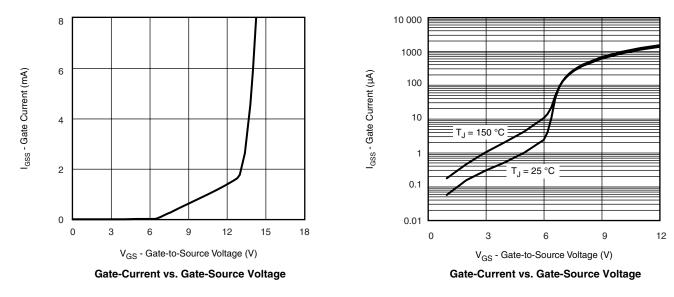
Notes:

a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



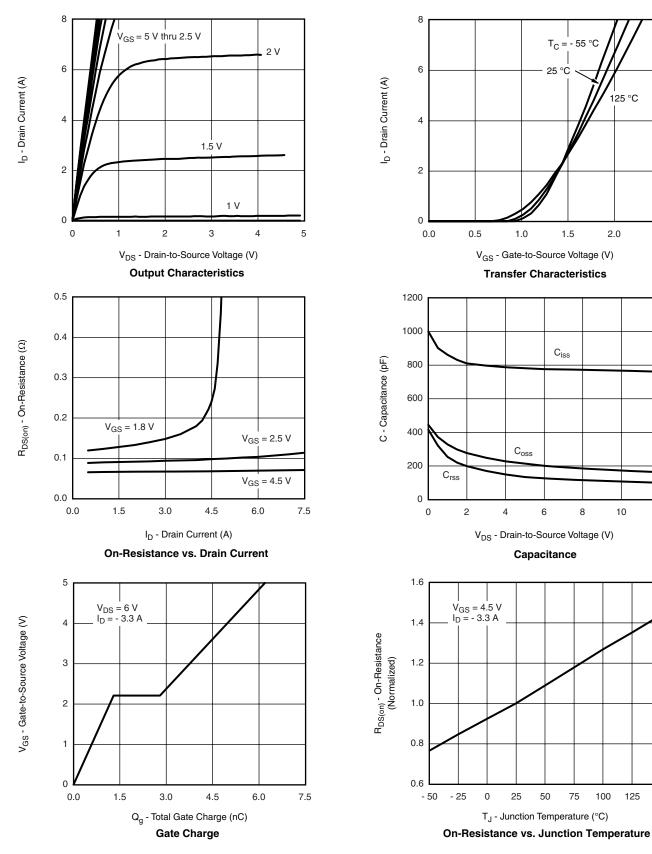


### Si1417EDH Vishay Siliconix

2.5

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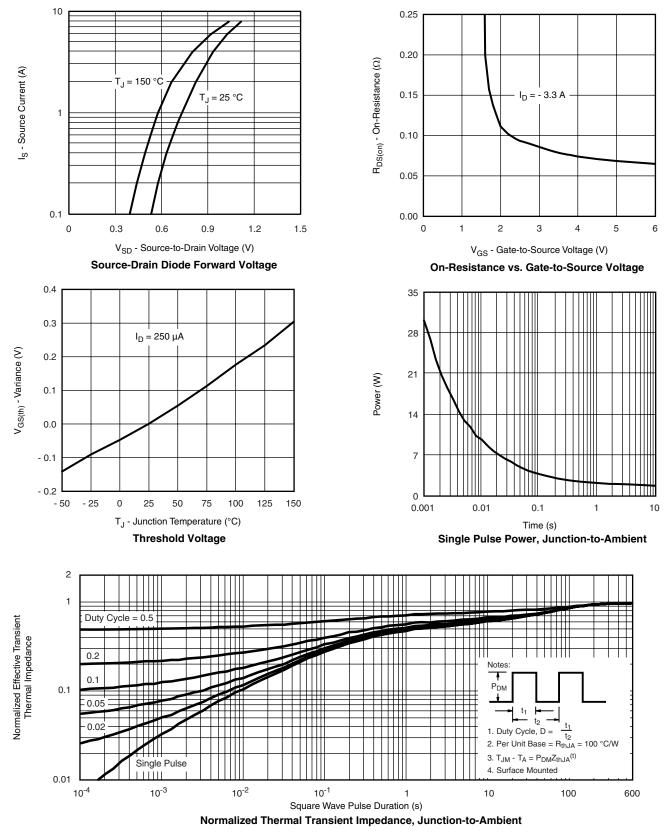
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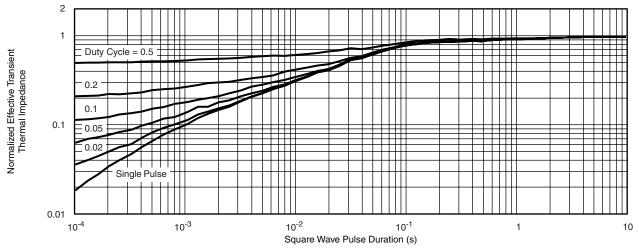




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Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg?71412</u>.



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